

1. Description

The SP001GBSDU400O02 is a 64M x 8bits Double Data Rate SDRAM high-density for DDR-400. The SP001GBSDU400O02 consists of 8pcs CMOS 64Mx8 bits Double Data Rate SDRAMs in 58 pin TSOP package, and a 2048 bits serial EEPROM on a 200-pin printed circuit board. The SP001GBSDU400O02 is a Dual In-Line Memory Module and is intended for mounting into 200-pin edge connector sockets. Synchronous design allows precise cycle control with the use of system clock. Data I/O transactions are possible on both edges of DQS. Range of operation frequencies, programmable latencies allow the same device to be useful for a variety of high bandwidth, high performance memory system applications.

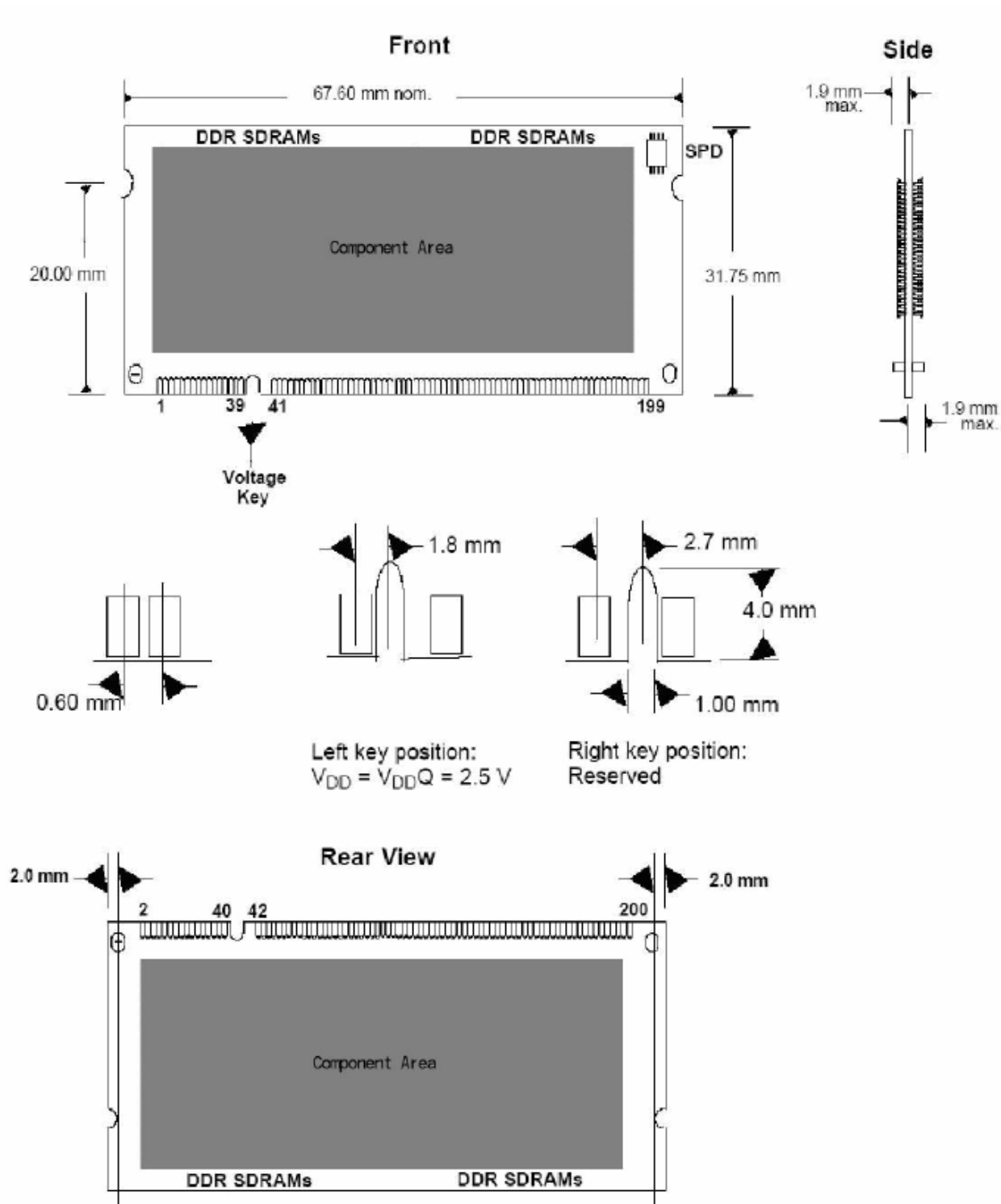
2. Features

- Double--data--rate architecture; two data transfers per clock cycle
- Bidirectional, data strobe (DQS) is transmitted/received with data, to be used in capturing data at the receiver
- DQS is edge--aligned with data for READs; center--aligned with data for WRITEs
- Differential clock inputs (CK and /CK)
- DLL aligns DQ and DQS transitions with CK transitions
- Commands entered on each positive CK edge; data and data mask referenced to both edges of DQS
- Four internal banks for concurrent operation
- Data mask (DM) for write data
- Burst lengths: 2, 4, or 8
- AUTOPRECHARGE option for each burst access
- Auto Refresh and Self Refresh Modes
- JEDEC standard 2.5 V (SSTL_2 compatible) I/O
- 58pin TSOP II Leaded & Pb-Free (RoHS compliant) package

3. Module Specification

Item	Specification
Capacity	1024MByte
Physical Bank(s)	2
Module Organization	128M x 64bit
Module Type	Unbuffered Non ECC
Speed Grade	PC-3200 / (DDR 400)
Voltage Interface	SSTL_2
Power Supply Voltage	2.6V±0.1V
Burst Lengths	4 or 8
DRAM Organization	64M x 8bit DDR SDRAM
PCB Layer	6Layers
Contact Tab	200 pin GOLD Flash Plating
Serial PD	Support

4. Simplified Mechanical Drawing with Keying Positions



5. Pinouts

Pin Num	Pin Name	Pin Num	Pin Name	Pin Num	Pin Name	Pin Num	Pin Name	Pin Num	Pin Name	Pin Num	Pin Name	Pin Num	Pin Name	Pin Num	Pin Name
1	VREF	51	VSS	101	A9	151	DQ42	2	VREF	52	VSS	102	A8	152	DQ46
3	VSS	53	DQ19	103	VSS	153	DQ43	4	VSS	54	DQ23	104	VSS	154	DQ47
5	DQ0	55	DQ24	105	A7	155	VDD	6	DQ4	56	DQ28	106	A6	156	VDD
7	DQ1	57	VDD	107	A5	157	VDD	8	DQ5	58	VDD	108	A4	158	/CK1
9	VDD	59	DQ25	109	A3	159	VSS	10	VDD	60	DQ29	110	A2	160	CK1
11	DQS0	61	DQS3	111	A1	161	VSS	12	DM0	62	DM3	112	A0	162	VSS
13	DQ2	63	VSS	113	VDD	163	DQ48	14	DQ6	64	VSS	114	VDD	164	DQ52
15	VSS	65	DQ26	115	A10/AP	165	DQ49	16	VSS	66	DQ30	116	BA1	166	DQ53
17	DQ3	67	DQ27	117	BA0	167	VDD	18	DQ7	68	DQ31	118	/RAS	168	VDD
19	DQ8	69	VDD	119	/WE	169	DQS6	20	DQ12	70	VDD	120	/CAS	170	DM6
21	VDD	71	NC	121	/S0	171	DQ50	22	VDD	72	NC	122	/S1	172	DQ54
23	DQ9	73	NC	123	NC	173	VSS	24	DQ13	74	NC	124	NC	174	VSS
25	DQS1	75	VSS	125	VSS	175	DQ51	26	DM1	76	VSS	126	VSS	176	DQ55
27	VSS	77	NC	127	DQ32	177	DQ56	28	VSS	78	NC	128	DQ36	178	DQ60
29	DQ10	79	NC	129	DQ33	179	VDD	30	DQ14	80	NC	130	DQ37	180	VDD
31	DQ11	81	VDD	131	VDD	181	DQ57	32	DQ15	82	VDD	132	VDD	182	DQ61
33	VDD	83	NC	133	DQS4	183	DQS7	34	VDD	84	NC	134	DM4	184	DM7
35	CK0	85	NC	135	DQ34	185	VSS	36	VDD	86	NC	136	DQ38	186	VSS
37	/CK0	87	VSS	137	VSS	187	DQ58	38	VSS	88	VSS	138	VSS	188	DQ62
39	VSS	89	CK2	139	DQ35	189	DQ59	40	VSS	90	VSS	140	DQ39	190	DQ63
41	DQ16	91	/CK2	141	DQ40	191	VDD	42	DQ20	92	VDD	142	DQ44	192	VDD
43	DQ17	93	VDD	143	VDD	193	SDA	44	DQ21	94	VDD	144	VDD	194	SA0
45	VDD	95	CKE1	145	DQ41	195	SCL	46	VDD	96	CKE0	146	DQ45	196	SA1
47	DQS2	97	NC	147	DQS5	197	VDDSP D	48	DM2	98	NC	148	DM5	198	SA2
49	DQ18	99	A12	149	VSS	199	VDDID	50	DQ22	100	A11	150	VSS	200	NC

6. Pin Description

SYMBOL	TYPE	DESCRIPTION
CK0-CK2, /CK0-/CK2	Input	Clock: CK and /CK are differential clock inputs. All address and control input signals are sampled on the crossing of the positive edge of CK and negative edge of /CK. Output data (DQs and DQS /DQS) is referenced to the crossings of CK and /CK.
CKE0, CKE1	Input	Clock Enable: CKE HIGH activates and CKE LOW deactivates the internal clock, input buffers and output drivers. Taking CKE LOW provides PRECHARGE POWER-DOWN and SELF REFRESH operations (all device banks idle), or ACTIVE POWERDOWN (row ACTIVE in any device bank). CKE is synchronous for POWER-DOWN entry and exit, and for SELF REFRESH entry. CKE is asynchronous for SELF REFRESH exit and for disabling the outputs. CKE must be maintained HIGH throughout read and write accesses. Input buffers (excluding CK, /CK and CKE) are disabled during POWER-DOWN. Input buffers (excluding CKE) are disabled during SELF REFRESH. CKE is an SSTL_2 input but will detect an LVCMOS LOW level after VDD is applied and until CKE is first brought to HIGH. After CKE has been brought HIGH, it is an SSTL_2 input only.
/S0, /S1	Input	Chip Select: Enables the associated SDRAM command decoder when low and disables the command decoder when high. When the command decoder is disabled, new commands are ignored but previous operations continue. Rank 0 is selected by S0; Rank 1 is selected by S1
/RAS, /CAS, /WE	Input	Command Inputs: /RAS, /CAS and /WE (along with /CS) define the command being entered.
DM0-DM7	Input	Input Data Mask: DM LOW allows WRITE operation. DM HIGH blocks WRITE operation. DM lines do not affect READ operation.
BA0 – BA1	Input	Bank Address Inputs: BA0 and BA1 define to which device bank an ACTIVE, READ, WRITE, or PRECHARGE command is being applied.
A0 - A12	Input	Address Inputs: Provide the row address for ACTIVE commands, and the column address and auto precharge bit (A10) for READ/WRITE commands, to select one location out of the memory array in the respective device bank. A10 sampled during a PRECHARGE command determines whether the PRECHARGE applies to one device bank (A10 LOW, device bank selected by BA0, BA1) or all device banks (A10 HIGH). The address inputs also provide the op-code during a MODE REGISTER SET command. BA0 and BA1 define which mode register (mode register or extended mode register) is loaded during the LOAD MODE REGISTER command.
DQ0-DQ63	Input/Output	Data bit Input/ Output: Bi-directional data bus.
DQS0-DQS7 /DQS0-/DQS7	Input/Output	Data Strobe: output with read data, input with write data for source-synchronous operation. Edge-aligned with read data, center-aligned with write data. For Rawcards using x16 organized DRAMs DQ0-7 connect to the LDQS pin of the DRAMs and DQ8-17 connect to the UDQS pin of the DRAM
NC		No Connect: No internal electrical connection is present.
VDDQ	Supply	Power supplies for the DDR2 SDRAM output buffers to provide improved noise immunity. For all current DDR2 unbuffered DIMM designs, VDDQ shares the same power plane as VDD pins
VDD, VSS	Supply	Power and ground for the DDR2 SDRAM input buffers, and core logic. VDD and VDDQ pins are tied to VDD / VDDQ planes on these modules.
VREF	Supply	Reference voltage for SSTL 18 inputs.
SDA	Input/Output	This bidirectional pin is used to transfer data into or out of the SPD EEPROM. A resistor must be connected from the SDA bus line to VDD to act as a pullup on the system board.
SCL	Input	This signal is used to clock data into and out of the SPD EEPROM. A resistor may be connected from the SCL bus time to VDD to act as a pullup on the system board.
VDDSPD	Supply	Power supply for SPD EEPROM. This supply is separate from the VDD / VDDQ power plane. EEPROM supply is operable from 1.7V to 3.6V.
SA0-SA2	Input	These signals are tied at the system planar to either VSS or VDD to configure the serial SPD EEPROM address range
VDDID		VDD Identification Flag